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Inclosure Material:

Metal all transistor

Overall Length:

0.833 inches all transistor

Mounting Facility Quantity:

1 all transistor

Internal Configuration:

Junction contact all transistor

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-60 all transistor

Internal Junction Configuration:

Npn all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

2 transistor

Mounting Method:

Threaded stud all transistor

Terminal Circle Diameter:

0.150 inches all transistor

Overall Width Across Flats:

0.430 inches all transistor

Thread Size:

0.190 inches all transistor

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

65.0 collector to base voltage, dc all transistor and 40.0 collector to emitter voltage, dc all transistor and 4.0 emitter to base voltage, dc all transistor

Current Rating Per Characteristic:

1.50 amperes source cutoff current all transistor and 200.00 milliamperes source cutoff current all transistor

Power Rating Per Characteristic:

11.6 watts small-signal input power, common-collector absolute all transistor

Maximum Operating Temperature Per Measurement Point:

200.0 degrees celsius junction all transistor

Thread Series Designator:

Unf all transistor

Terminal Type And Quantity:

3 pin all transistor

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fig:

A110a0